

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S17 0	2143	(438/208,107,109,4,928,915,187,209,203,86,195).CCLS.	USPAT; USOCR	OR	OFF	2005/07/28 15:10
S17 1	6	S170 and "MCM type"	US-PGPUB; USPAT	OR	ON	2005/07/28 15:12
S17 2	98	S170 and "die bonding"	US-PGPUB; USPAT	OR	ON	2005/07/28 15:29
S17 3	3	S170 and "compact semiconductor device"	US-PGPUB; USPAT	OR	ON	2005/07/28 15:39
S17 4	139	S170 and "mcm"	US-PGPUB; USPAT	OR	ON	2005/07/28 15:41
S17 5	2824	(257/723,787).CCLS.	USPAT; USOCR	OR	OFF	2005/07/29 12:32
S17 6	52	S175 and "insulation film"	US-PGPUB; USPAT	OR	ON	2005/07/29 12:41
S17 7	0	S176 and "single-layer"	US-PGPUB; USPAT	OR	ON	2005/07/29 12:33
S17 8	11	S176 and "die bonding"	US-PGPUB; USPAT	OR	ON	2005/07/29 12:34
S17 9	2140	(257/758,759).CCLS.	USPAT; USOCR	OR	OFF	2005/07/29 15:36
S18 0	21	S179 and "die bonding"	US-PGPUB; USPAT	OR	ON	2005/07/29 15:41
S18 1	239	S179 and insulation with film	US-PGPUB; USPAT	OR	ON	2005/07/29 16:04
S18 2	15	((("4630096") or ("4746960") or ("4827328") or ("4860166") or ("4866508") or ("4878991") or ("4884122") or ("4894115") or ("4907062") or ("4933042") or ("5049980") or ("5091769") or ("5111278") or ("5144747") or ("5250843"))).PN.	USPAT; USOCR	OR	OFF	2005/07/29 16:09
S18 3	1947	(257/758).CCLS.	USPAT; USOCR	OR	OFF	2005/08/01 08:39
S18 4	5189	((257/685,687,90,723,787) or (438/107,118)).CCLS.	USPAT; USOCR	OR	OFF	2005/08/01 08:40
S18 6	404	S184 and (remove or removal) with substrate	US-PGPUB; USPAT	OR	ON	2005/08/01 09:39
S18 7	133	S184 and substrate adj1 (remove or removal or removed)	US-PGPUB; USPAT	OR	ON	2005/08/01 10:43
S18 8	6	S184 and Si adj substrate adj1 (remove or removal or removed)	US-PGPUB; USPAT	OR	ON	2005/08/01 10:44
S18 9	1	("6159767").PN.	USPAT; USOCR	OR	OFF	2005/08/01 15:50

S19 0	10710	MCM	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 13:43
S19 1	165	S190 and ((target adj mark) or (alignment adj mark))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:01
S19 2	2	S191 and "third insulation film"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:10
S19 3	16121	("multi-chip" or multichip)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 14:04
S19 4	23537	("multi-chip" or multichip or (plurality adj chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 14:05
S19 5	602	S194 and ((target adj mark) or (alignment adj mark))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 14:05
S19 6	411	S195 and (via or "connection hole" or interconnect)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 14:12
S19 7	2	S196 and "third insulation film"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 14:07
S19 8	10	S196 and "insulation film"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 14:07
S19 9	5	S191 and ("insulation film" same layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:00

S20 0	664	"third insulation film"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:50
S20 1	8	S200 and ((target adj mark) or (alignment adj mark))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:01
S20 2	0	S191 and "third insulation layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:11
S20 3	11390	((first or second or third) same "insulation film")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:11
S20 4	88	S203 and (plurality adj chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:47
S20 5	23	S204 and ((target adj mark) or (alignment mark))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:12
S20 6	8	S200 and (plurality adj chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/30 15:47
S20 7	23569	("multi-chip" or multichip or (plurality adj chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 13:11
S20 8	603	S207 and ((target adj mark) or (alignment adj mark))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 15:57
S20 9	432	S208 and (substrate same chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 13:37

S21 0	297	S207 and (((target adj mark) or (alignment adj mark)) same chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 13:39
S21 1	545	(((target adj mark) or (alignment adj mark)) same (substrate same chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 14:15
S21 2	353	S211 and @pd<"20031120"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 15:25
S21 3	364	S208 and @pd<"20031120"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 15:25
S21 4	107	S207 and ("alignment mark" adj3 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 15:37
S21 5	107	S207 and (((target adj mark) or (alignment adj mark)) adj3 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 16:03
S21 6	2	"alignment mark in"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/01/31 16:04